NSN 5962-01-226-3922

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-226-3922 **Body Length:** 0.840 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 794.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** An/bps14to15e **Features Provided:** Hermetically sealed and burn in and programmable and bipolar and schottky **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:**

input on ouit i

10 input

Case Outline Source And Designator:

D-2 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

85.00 nanoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Prom

Memory Capacity:

Unknown

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

NSN 5962-01-226-3922

Memory Microcircuit - Page 2 of 2



	• •				
In	18	<i>(</i>)+	МА	261	ıre:

--

Demilitarization:

Yes - demil/mli

Fiig:

A458a0